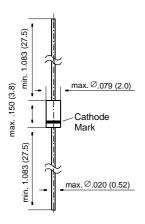
BAT41

Schottky Diodes

DO-35



Dimensions in inches and (millimeters)

FEATURES

- ♦ For general purpose applications
- This diode featutres low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in a MiniMELF case with type designation LL41.

MECHANICAL DATA

Case: DO-35 Glass Case Weight: approx. 0.13 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	100	V	
Forward Continuous Current at T _{amb} = 25 °C	IF	1001)	mA	
Repetitive Peak Forward Current at t _p < 1 s, @ < 0.5, T _{amb} = 25 °C	I _{FRM}	3501)	mA	
Surge Forward Current at $t_p = 10$ ms, $T_{amb} = 25$ °C	I _{SFM}	750 ¹⁾	mA	
Power Dissipation, T _{amb} = 25 °C	P _{tot}	4001)	mW	
Junction Temperature	T _j	125	°C	
Ambient Operating Temperature Range	T _{amb}	-65 to +125	°C	
Storage Temperature Range	T _S	-65 to +150	°C	

1) Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.



BAT41

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA / 300 μs Pulses	V _{(BR)R}	100	110	_	V
Forward Voltage Pulse Test t_p = 300 μ s at I_F = 1 mA at I_F = 200 mA	V _F V _F		0.40	0.45 1.0	V
Leakage Current Pulse Test t_p = 300 μ s at V_R = 50 V, at T_j = 25 °C at V_R = 50 V, at T_j = 100 °C	I _R			100 20	nA μA
Capacitance at V _R = 1 V, f = 1 MHz	C _{tot}	-	2	_	pF
Reverse Recovery Time from $I_F = 10$ mA, to $I_R = 10$ mA to $I_R = 1$ mA $I_R = 100$ Ohm	t _{rr}	-	5	_	ns
Thermal Resistance Junction to Ambient Air	R _{thJA}	_	_	3001)	K/W

¹⁾ Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.

